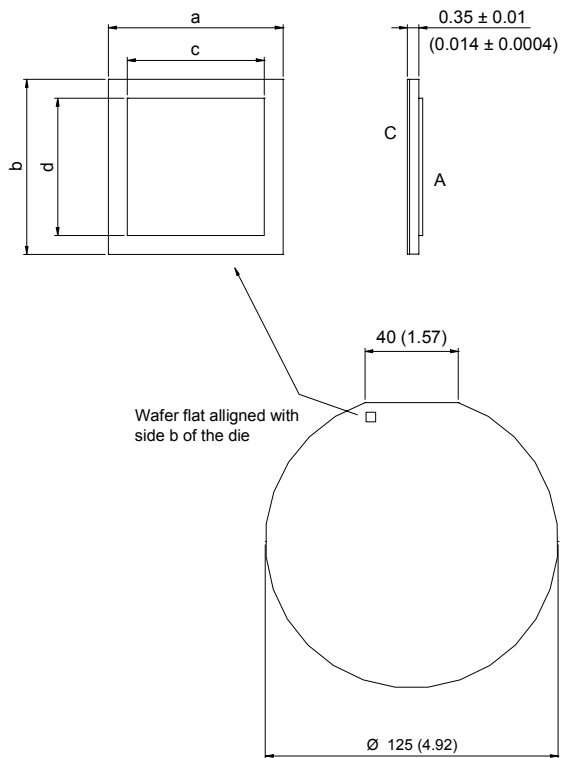


International
IOR Rectifier

FD100H06A5B

Fred Die in Wafer Form



NOTES:

1. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

2. CONTROLLING DIMENSION (INCH):

3. DIMENSIONS AND TOLERANCES:

a = 2.540 ± 0.05

(0.100 ± 0.002)

b = 2.540 ± 0.05

(0.100 ± 0.002)

c = 1.880 ± 0.003

(0.074 ± 0.0001)

d = 1.880 ± 0.003

(0.074 ± 0.0001)

4. LETTER DESIGNATION:

A = Anode (Top Metal)

C = Cathode (Back Metal)

5. SAWING:

Recommended Blade

SEMITEC S1025 QS00 Blade

6. MINIMUM ORDER QUANTITY:

1300 die

NOT TO SCALE

Reference IR Packaged Part: 8ETH06 Series

Electrical Characteristics (Wafer Form)

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	2.3 V	$T_J = 25^\circ\text{C}$, $I_F = 8\text{ A}$
V_{RRM} Minimum Reverse Breakdown Voltage	600 V	$T_J = 25^\circ\text{C}$, $I_{RRM} = 200\text{ }\mu\text{A}$
I_{RM} Max. Reverse Leakage Current	100 μA	$T_J = 25^\circ\text{C}$, $V_{RRM} = 600\text{ V}$
t_{rr} Typ. Reverse Recovery Time	20 ns	$I_F = 1\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_R = 30\text{ V}$

Mechanical Data

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 2 KA - 3 KA)
Nominal Front Metal Composition, Thickness	99% Al, 1% Si (3 microns)
Chip Dimensions	0.100" x 0.100" (see drawing)
Reject Ink Dot Size	0.25 mm diameter minimum
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

FD	100	H	06	A	5	B
①	②	③	④	⑤	⑥	⑦

- 1** - Fred Die
- 2** - Chip Dimension in Mils: 100 = 100x100 square
- 3** - Process H = HyperFast
- 4** - Voltage code V_{rrm} (*100) eg: 06 = 600V
- 5** - Chip surface metallization: A = Aluminium (anode), Silver (cathode)
- 6** - Wafer diameter in inches
- 7** - Packaging: B = Inked Probed Unsawn Wafer (Wafer in box)